What is claimed is:

1. An organic EL device comprising:

a lower electrode formed on a substrate;

an organic EL /ayer formed on the lower electrode;

an upper electrode formed on the organic EL layer; \_\_\_\_\_

5 a sealing member for sealing said lower electrode,

6 organic EL layer and upper electrode on said substrate so that

7 they are covered with the sealing member, wherein said sealing

8 member is made of an aluminum material coated with an insulating

9 layer in its/inner surface.

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1 2. An organic EL device according to claim 1, wherein said

aluminum material is a flexible aluminum sheet.

1 3. An organic El device according to claim 1, wherein said

2 insulating layer is an aluminum oxide layer formed by anodic

3 oxidation of said aluminum material.

1 4. An organic EL device according to claim 1, wherein said

2 insulating layer is a porous aluminum oxide layer.

1 5. An organic EL device according to claim 3, wherein said

2 aluminum sheet is formed in such a manner that a surface of said

3 aluminum oxide layer is subjected  $igl( ext{to gas flow-out treatment in}igl)$ 

- 4 vacuum, and thereafter said lower electrode, organic EL layer and
- 5 upper electrode are sealed on the substrate in an atmosphere of
- 6 inert gas.

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- 1 -6. A method of manufacturing an organic EL device
- 2 comprising the steps of:
- forming a lower electrode formed on a substrate;
- forming an organic EL layer on the lower electrode;
- forming an upper electrode on the organic EL layer to
- 6 provide the organic EL device;
- 7 preparing an aluminum material coated with an insulating
- 8 layer in at least its inner surface; and
- 9 sealing said organic EL device so that it is covered with
- 10 said aluminum material.
  - 1 7. A method of manufacturing an organic EL device according
  - 2 to claim 6, wherein
  - 3 said step of preparing the aluminum material comprises
  - 4 the steps of:
  - 5 making anodic oxidation to form an aluminum oxide layer
  - 6 on a surface of a flexible aluminum sheet; and
  - 7 removing gas contained within said aluminum oxide layer,
  - 8 and
  - 9 said step of sealing said organic EL device comprises the
- 10 step of:

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- fixing said aluminum sheet with the gas removed on a 12 surface of said substrate in an atmosphere of inert gas or in
- 13 vacuum.

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- A method of manufacturing an organic EL device according 1 8.
- 2 to\_claim 1, wherein\_said step of removing\_gas is to heat\_the
- aluminum sheet with the aluminum oxide layer for several-60 3
- 4 minutes at 60-300 °C in vacuum.
- A method of manufacturing an organic EL device according 1 9.
- 2 to claim 7, wherein said step of making anodic oxidation is to
- form a porous aluminum oxide layer; and
- said step of removing gas is to heat said aluminum sheet
- 5 in vacuum so that impurities contained in pores of said porous
- aluminum oxide layer are discharged.
- 1 10. A method of manufacturing an organic EL device according
- 2 to claim 7, wherein
- 3 said step of sealing said organic EL device comprises the steps
- 4 of:
- 5 mounting said organic EL device and aluminum sheet in a
- 6 sealing chamber and once heating them at room temperature- 150
- 7 °C in vacuum;
- 8 introducing inert gas into the sealing chamber; and
- 9 fixing said aluminum sheet to said substrate through an

- 1 11. A method of manufacturing an organic EL device according
- 2 to claim 7, wherein said inert gas is argon gas.

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